

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Applications

- Power management in half bridge and inverters
- DC-DC Converter
- Load Switch

General Description

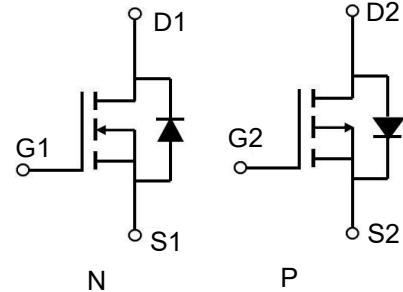
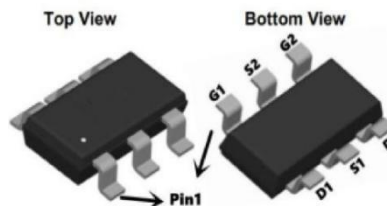
The XXW6G03 is the highest performance trenchN-ch and P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The XXW6G03 meet the RoHS and Green Product requirement , 100% EAS guaranteedwith full function reliability approved.

Product Summary

BVDSS	RDSON	ID
30V	18mΩ	6A
-30V	36mΩ	-6A

SOT23-6LPin Configurations



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	30	-30	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6.0	-6	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	5	-4	A
I_{DM}	Pulsed Drain Current ²	20	-12	A
EAS	Single Pulse Avalanche Energy ³	72	59	mJ
I_{AS}	Avalanche Current	21	-19	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	2.5	2.08	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	50	$^\circ C/W$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.034	---	V/ $^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=6A$	---	18	25	m Ω
		$V_{GS}=4.5V, I_D=5A$	---	25	31	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.8	---	mV/ $^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V, T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=30V, V_{GS}=0V, T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=15V, I_D=5A$	---	10	---	S
R_g	Gate Resistance	$V_{DS}=24V, V_{GS}=0V, f=1MHz$	---	2.5	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=20V, V_{GS}=4.5V, I_D=6A$	---	7.2	---	nC
Q_{gs}	Gate-Source Charge		---	1.4	---	
Q_{gd}	Gate-Drain Charge		---	2.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=12V, V_{GS}=10V, R_G=3.3\Omega$ $I_D=5A$	---	3.9	---	ns
T_r	Rise Time		---	9.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	14.5	---	
T_f	Fall Time		---	6.0	---	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1MHz$	---	370	---	pF
C_{oss}	Output Capacitance		---	54	---	
C_{rss}	Reverse Transfer Capacitance		---	40	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	$V_{DD}=25V, L=0.1mH, I_{AS}=10A$	16	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current	---	---	6	A
I_{SM}	Pulsed Source Current ^{2,6}		---	---	20	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=5A, T_J=25^{\circ}\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, $t < 10\text{sec}$.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=10A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The Min. value is 100% EAS tested guarantee.
- 6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V	-	-	-1	μA
Gate-Source Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Gate-Source Threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1	-1.5	-2.5	V
Drain-Source on-State Resistance ³	R _{DS(on)}	V _{GS} = -10V, I _D = -4.1A	-	36	60	mΩ
		V _{GS} = -4.5V, I _D = -3A	-	50	85	
Dynamic Characteristics ⁴						
Input Capacitance	C _{iss}	V _{GS} = 0V , V _{DS} = -15V, f = 1.0MHz	-	530	-	pF
Output Capacitance	C _{oss}		-	70	-	
Reverse Transfer Capacitance	C _{rss}		-	56	-	
Switching Characteristics ⁴						
Total Gate Charge	Q _g	V _{GS} = -10V, V _{DS} = -15V, I _D = -4.1A	-	6.8	-	nC
Gate–Source Charge	Q _{gs}		-	1.0	-	
Gate–Drain Charge	Q _{gd}		-	1.4	-	
Turn-on Delay Time	t _{d(on)}	V _{GS} = -10V, V _{DS} = -15V , R _L = 15Ω,R _{GEN} = 2.5Ω	-	14	-	ns
Rise Time	t _r		-	61	-	
Turn-off Delay time	t _{d(off)}		-	19	-	
Fall Time	t _f		-	10	-	
Source-Drain Body Diode Characteristics						
Diode Forward Voltage ³	V _{SD}	I _S = -4.1A, V _{GS} = 0V	-	-	-1.2	V
Continuous Source Current	I _S		-	-	-6.0	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$.
2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. This value is guaranteed by design hence it is not included in the production test.

N-Channel Typical Characteristics

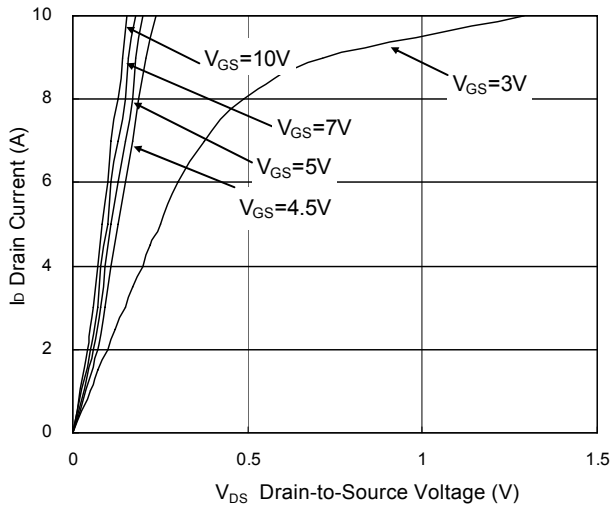


Fig.1 Typical Output Characteristics

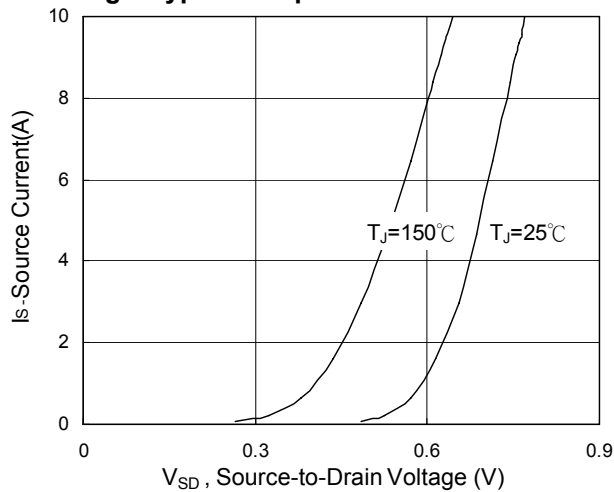
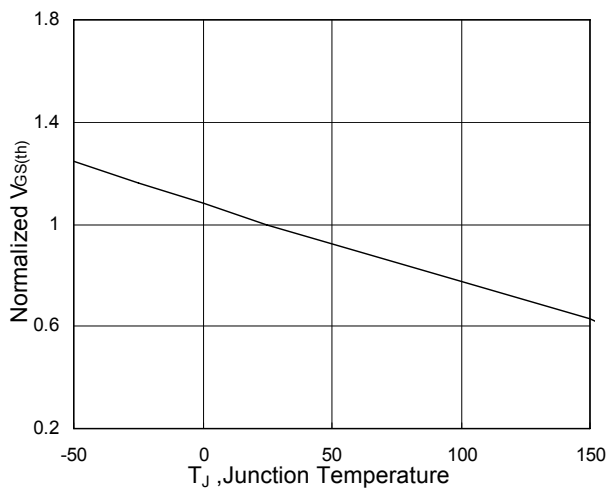


Fig.3 Forward Characteristics of Reverse



(°C) Fig.5 $V_{GS(th)}$ vs. T_J

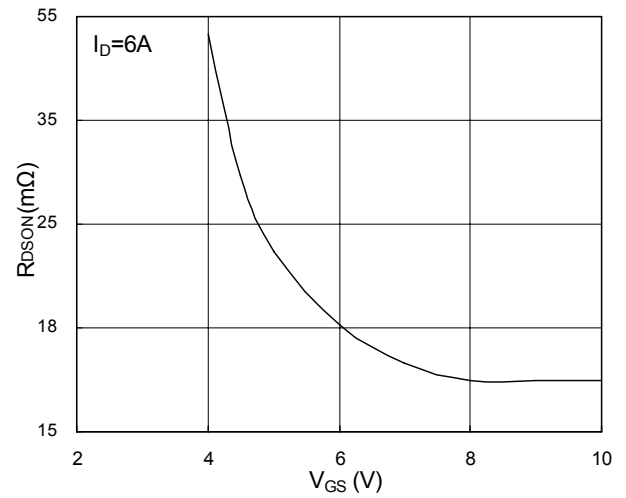


Fig.2 On-Resistance vs. G-S Voltage

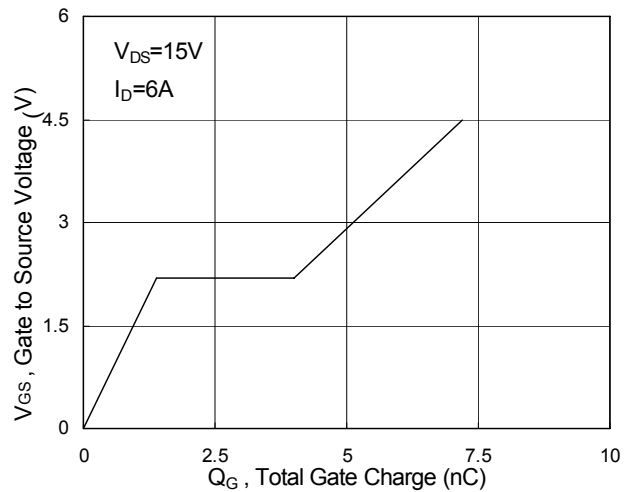


Fig.4 Gate-charge Characteristics

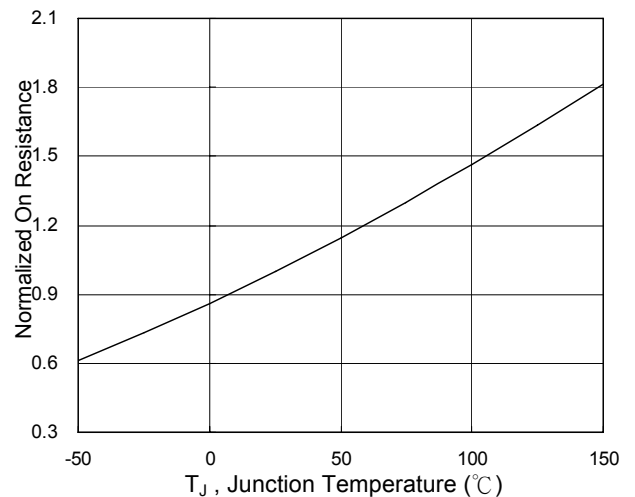


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

N-Ch and P-Ch Fast Switching MOSFETs

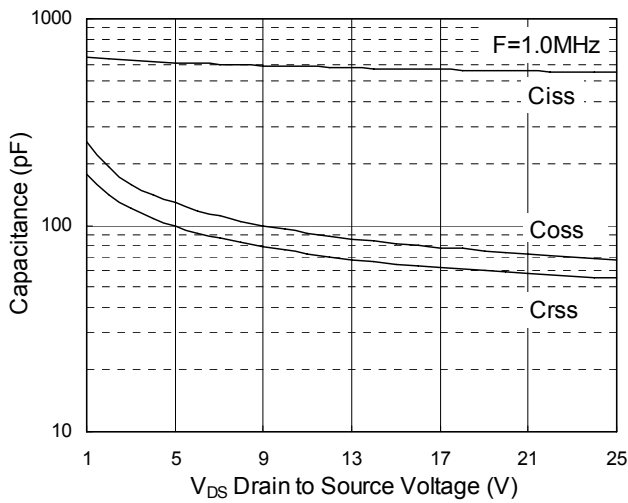


Fig.7 Capacitance

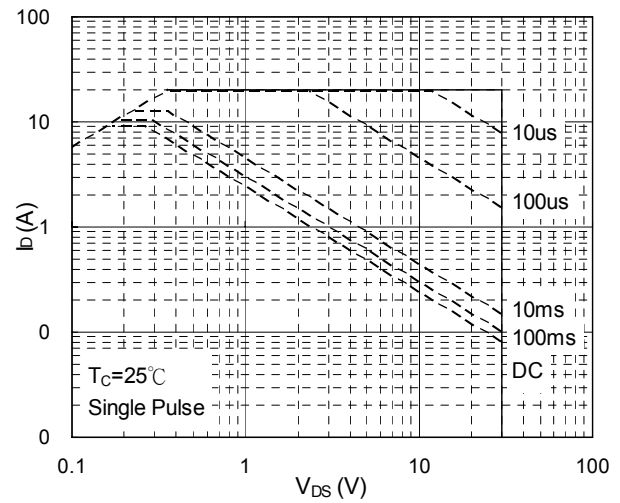


Fig.8 Safe Operating Area

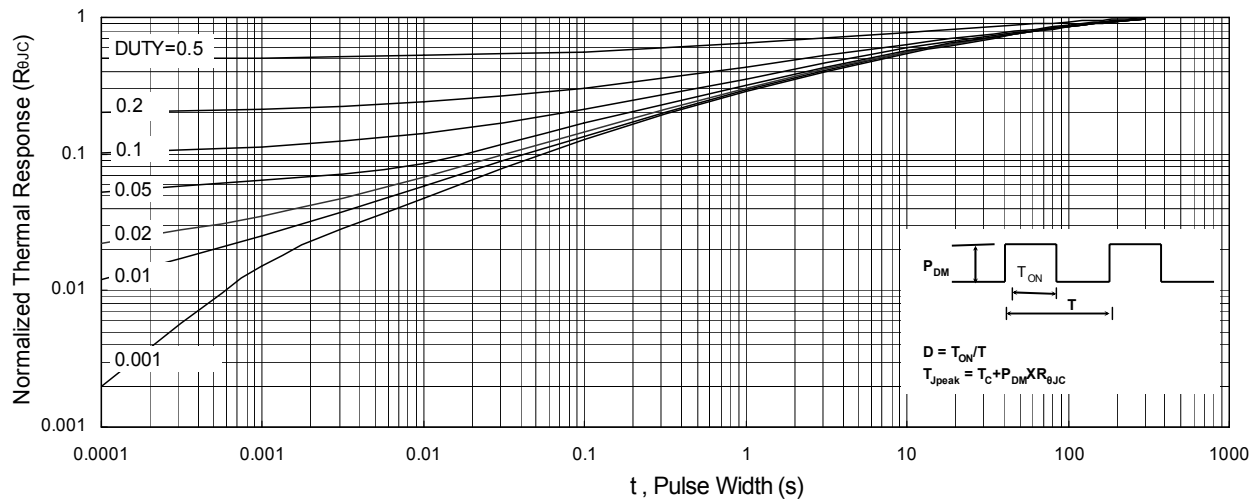


Fig.9 Normalized Maximum Transient Thermal Impedance

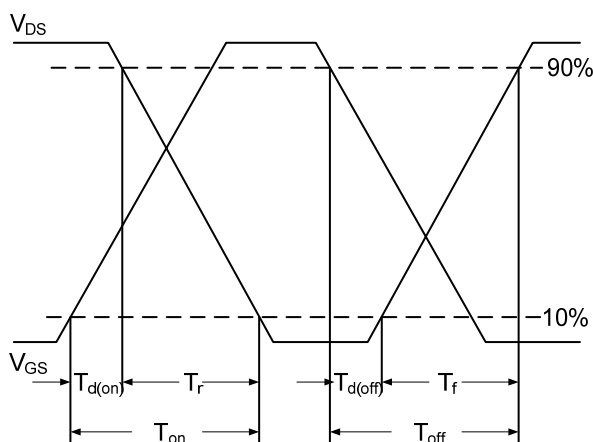


Fig.10 Switching Time Waveform

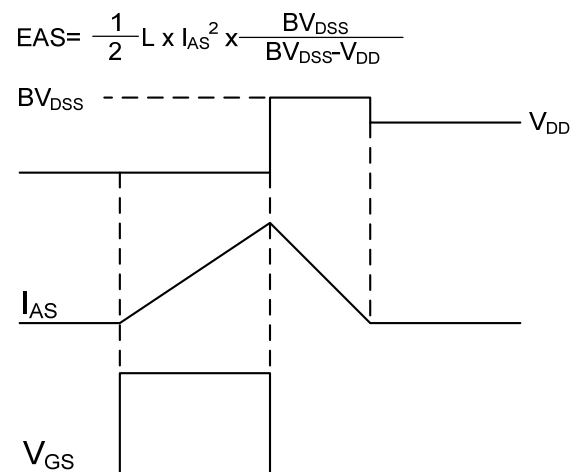


Fig.11 Unclamped Inductive Waveform

P-Channel Typical Characteristics

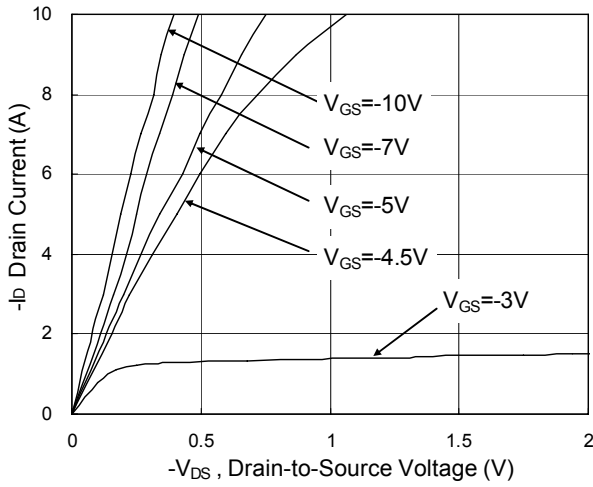


Fig.1 Typical Output Characteristics

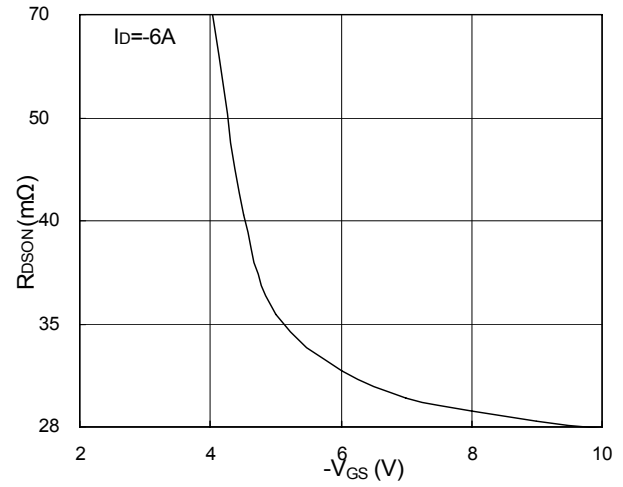


Fig.2 On-Resistance vs. Gate-Source

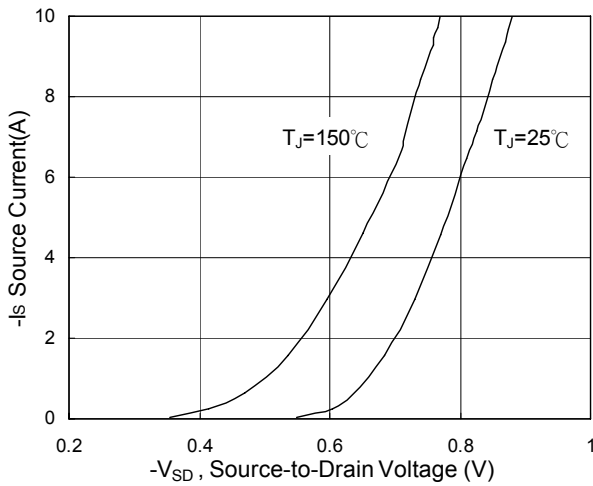


Fig.3 Forward Characteristics of Reverse

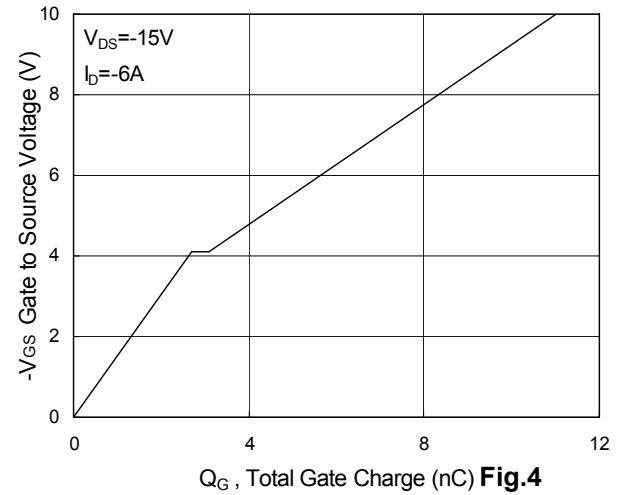


Fig.4

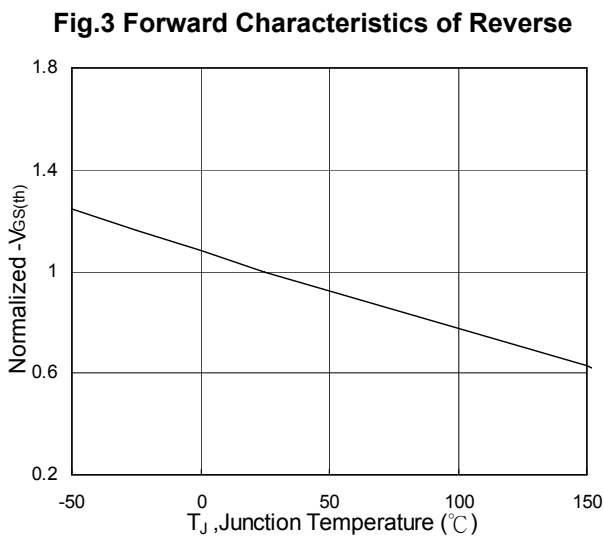


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

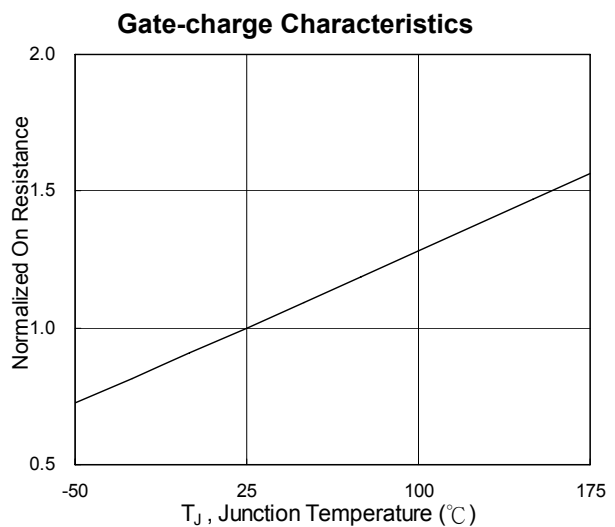


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

N-Ch and P-Ch Fast Switching MOSFETs

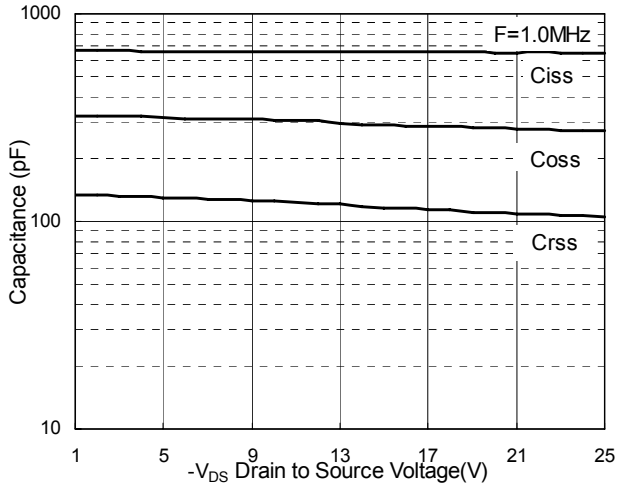


Fig.7 Capacitance

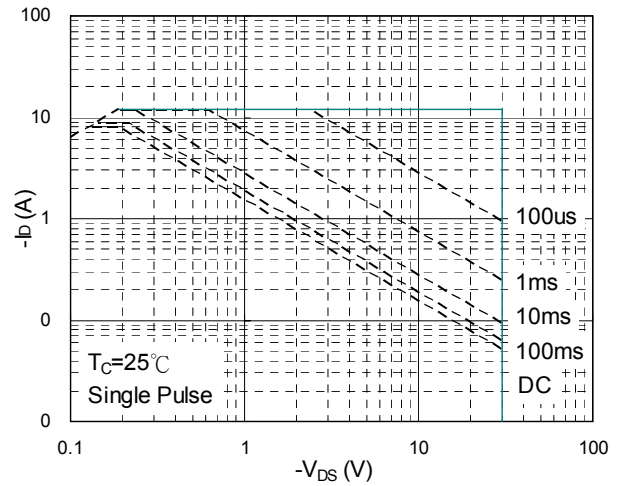


Fig.8 Safe Operating Area

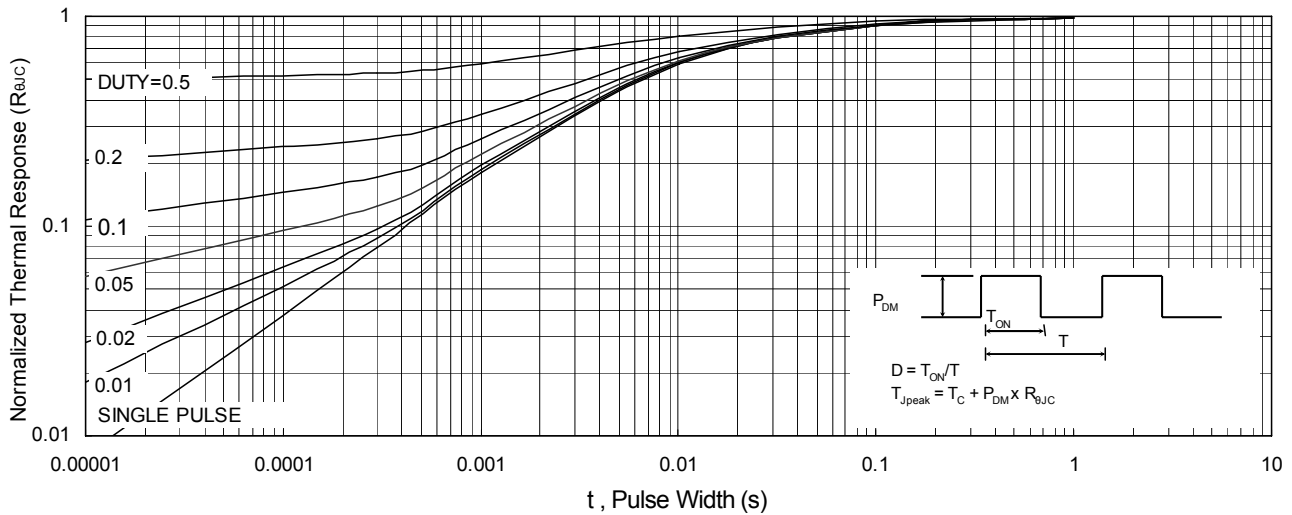


Fig.9 Normalized Maximum Transient Thermal Impedance

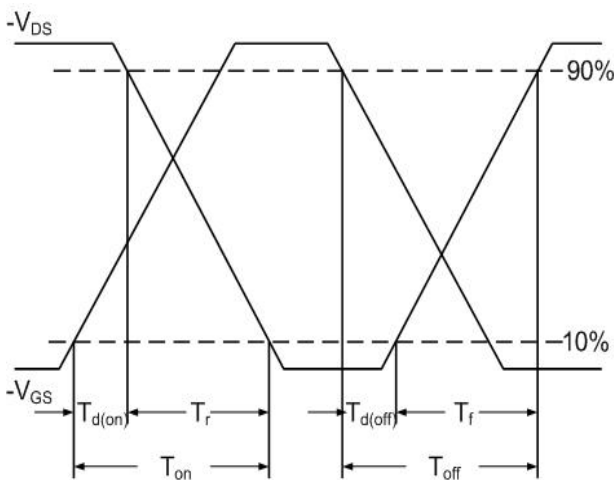


Fig.10 Switching Time Waveform

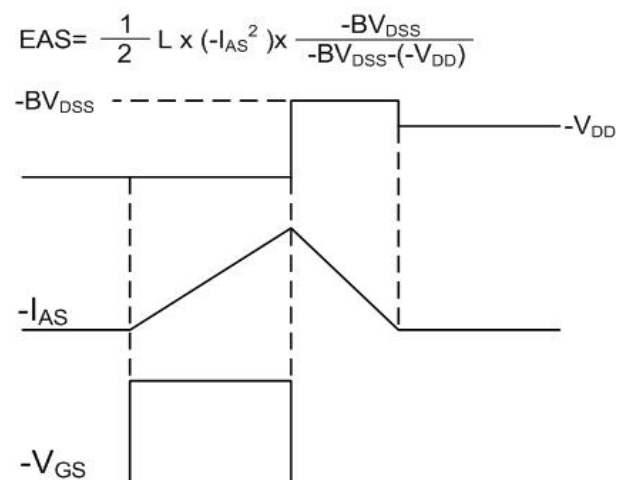
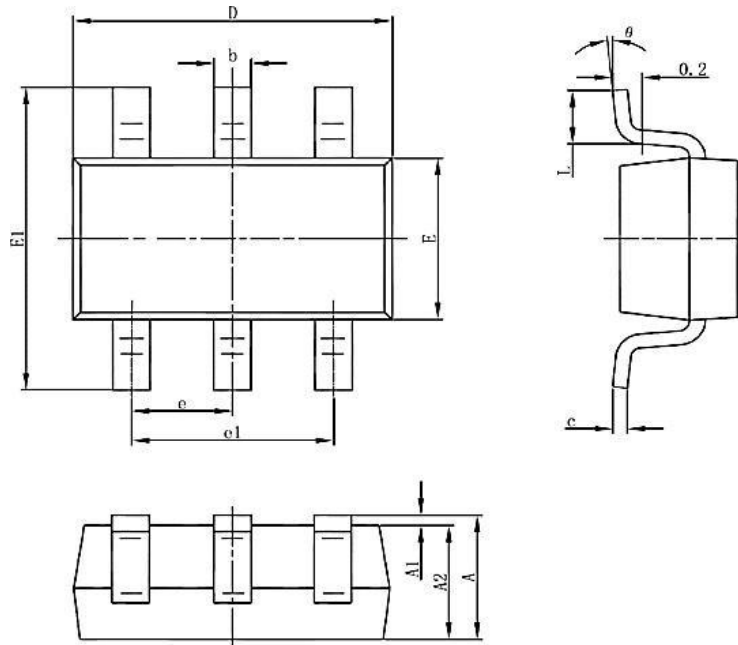


Fig.11 Unclamped Inductive Waveform

SOT23-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
C	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950 (BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0	8	0	8